

# Design for Manufacturability (DFM)

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聲明

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## Design for Manufacturability (DFM)

- Consider the following issues to increase manufacturing yield
  - Crosstalk/Signal Integrity (SI)
  - Gate oxide integrity
    - Antenna fixing
  - Via resistance and reliability
    - Extra contacts
  - Metal erosion
    - Metal slotting
  - Metal liftoff
    - Metal slotting
  - Metal over-etching
    - Metal fill

#### SI/Crosstalk Problem

SI: signal integrity

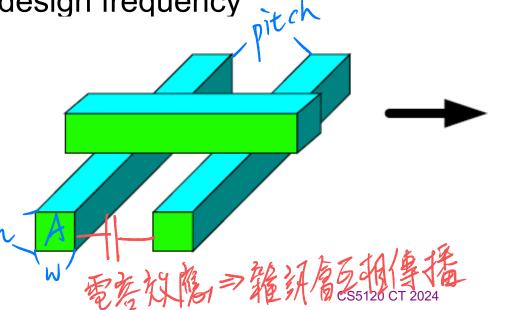
 Crosstalk problem are getting more serious in 0.25um and below More Serios  $R \propto \frac{PL}{A} \Rightarrow \frac{P \times 0.7L}{0.7h \times 0.7W} = 1.4R$  製程版編後

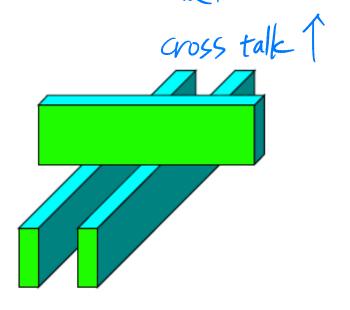
for:

Smaller pitches

Greater height/width ratio

Higher design frequency





#### SI/Crosstalk Problem

Delay problem

**Aggressor** 

**Aggressor** 

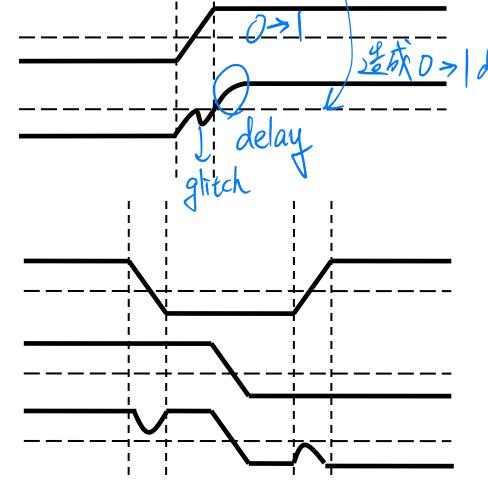
**Original signal** 

Impacted signal

/ Original signal

Impacted signal

Noise problem



cross tak

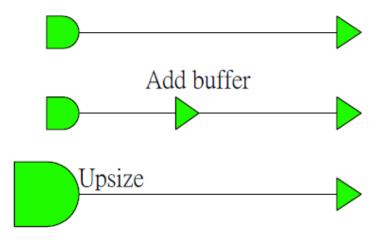
#### SI/Crosstalk Prevention

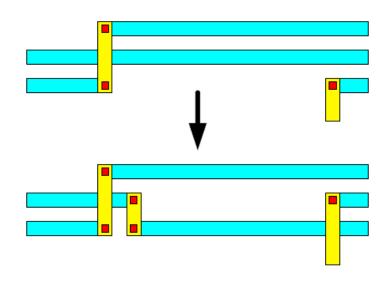
#### Placement solution

- Insert buffer in lines
- Upsize driver
- Congestion optimization

#### Routing solution

- Limit length of parallel nets
- Wider routing grid
- Shield special nets



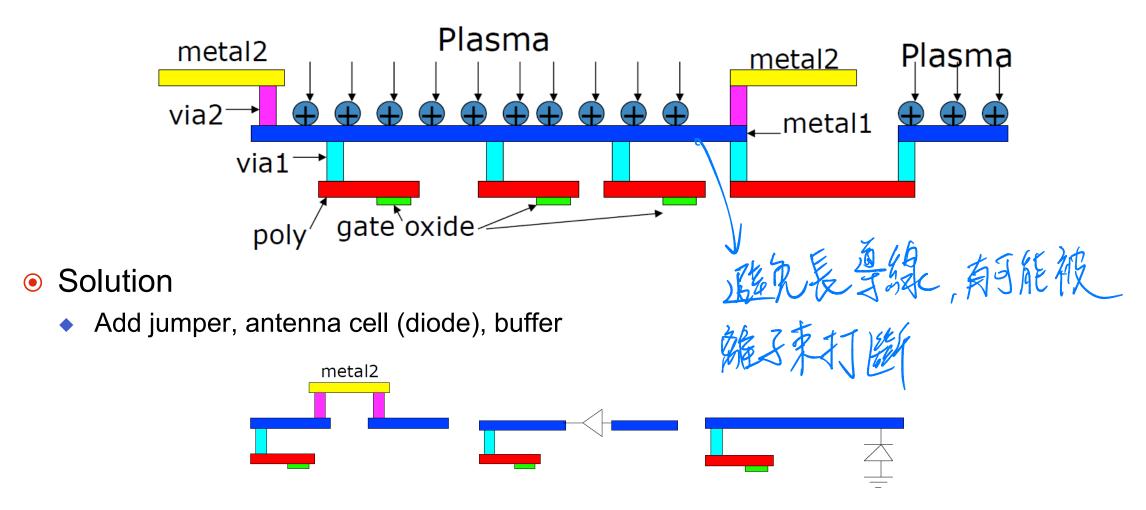


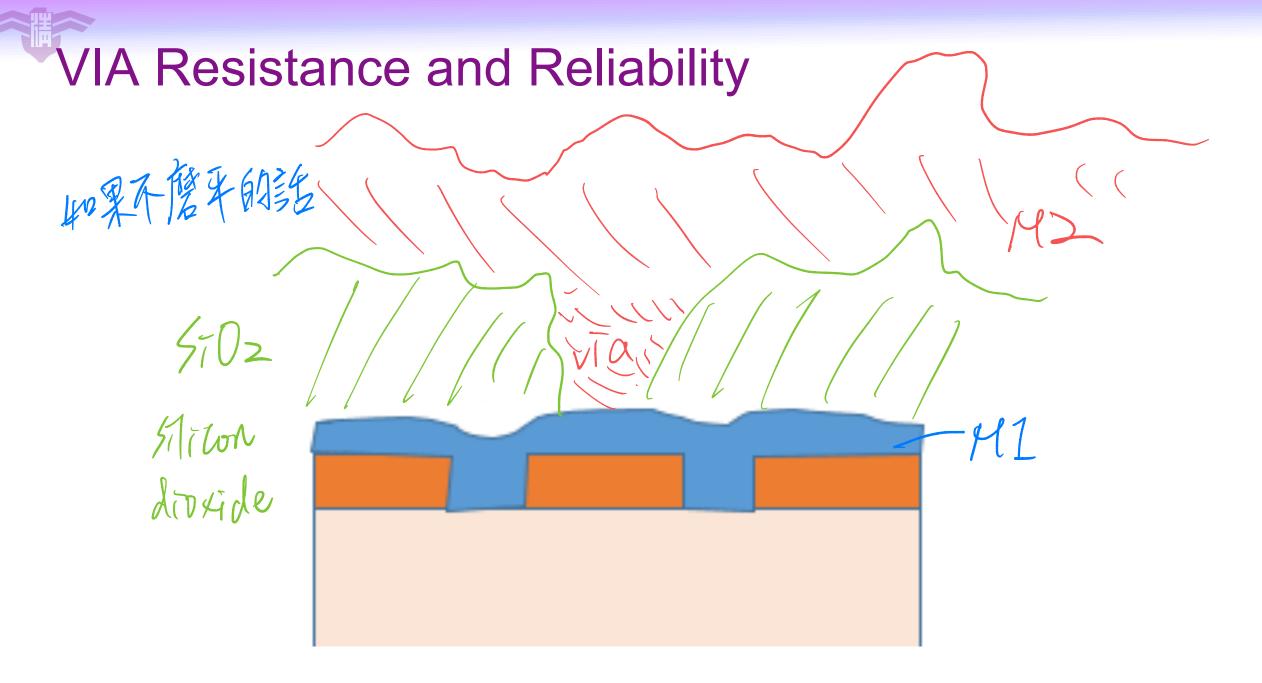
#### Antenna Effect

- In a chip manufacturing process, metal is initially deposited so it covers the entire chip.
- Then, the unneeded portions of the metal are removed by etching, typically in plasma (charged particles).
- The exposed metal collect charge from plasma and form voltage potential.
- If the voltage potential across the gate oxide becomes large enough, the current can damage the gate oxide.

#### Process Antenna Problem

Process antenna problem may destroy the circuit after a period of time





#### **CMP Process**

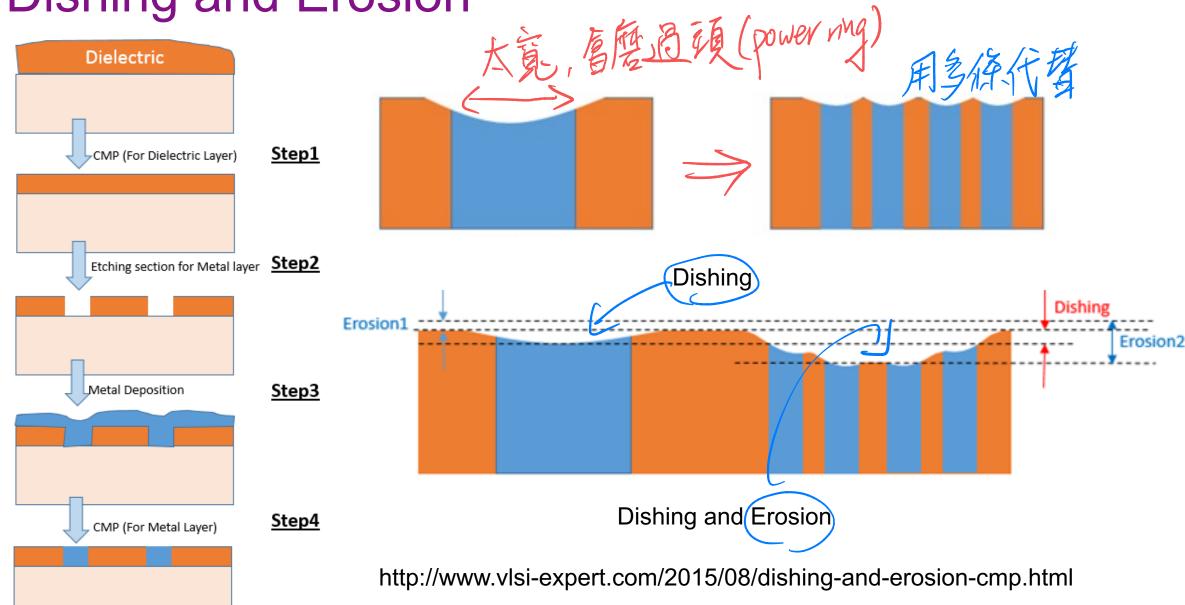
- Chemical Mechanical Polishing (CMP) process
- Metal erosion
  - Metal is mechanically softer than dielectric
    - Dishing
    - Erosion
  - Maximum metal density per layer
    - Rule to minimize erosion

Step1 CMP (For Dielectric Layer) Etching section for Metal layer Step2 Metal Deposition Step3 Step4 , CMP (For Metal Layer)

Dielectric

http://www.vlsi-expert.com/2015/08/dishing-and-erosion-cmp.html

Dishing and Erosion



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#### **Metal Liftoff**

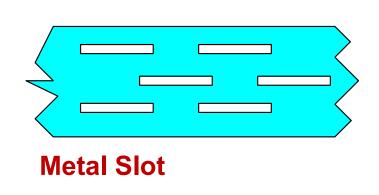
- Conductor and dielectric with different coefficients of thermal expansion
  - Metal can lift off with time
  - Wider metal are more vulnerable

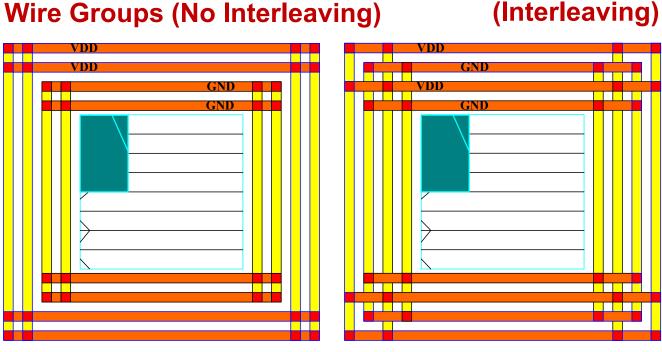


- Maximum metal density per layer
  - Rule to minimize metal liftoff

#### Metal Slotting or Wire Grouping for Wide Metal Wires

- Reduce the metal density
- Primarily used for power and ground traces
  - Any others if wide enough
- Different slotting parameters layer by layer

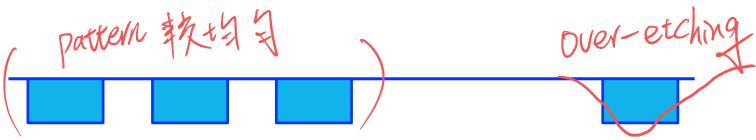




## **Metal Over-Etching**

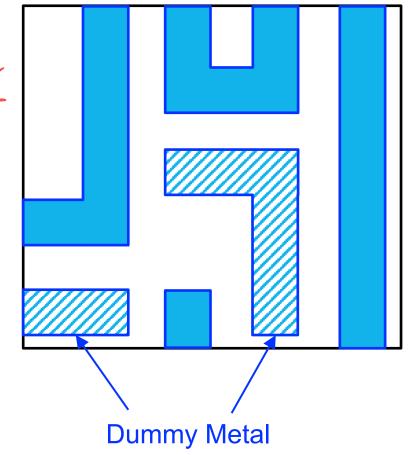
A narrow metal wire separated from other metal

More vulnerable for over-etching



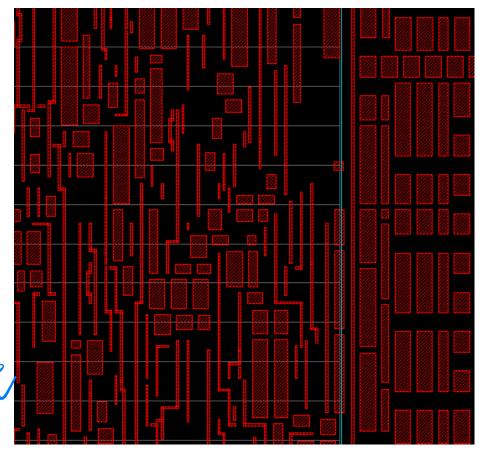


- Solution: metal fill
  - Limit the antenna fixing



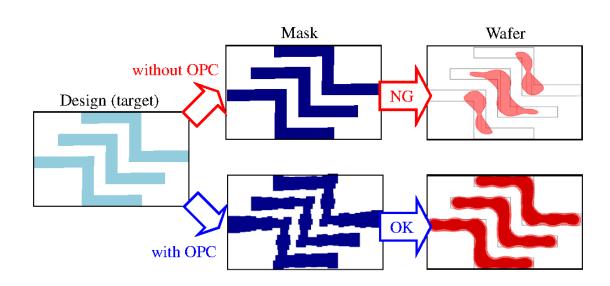
# Dummy Metal meta fil

- Why add dummy
  - Meet minimize metal density rule
  - Prevent over etching
  - Prevent sagging in local area
  - Improve yield
  - Reduce on chip variation
- Better connect dummy metal to VSS
- Side effect 可能增加 antema effect
  - Introduce parasitic to signal line

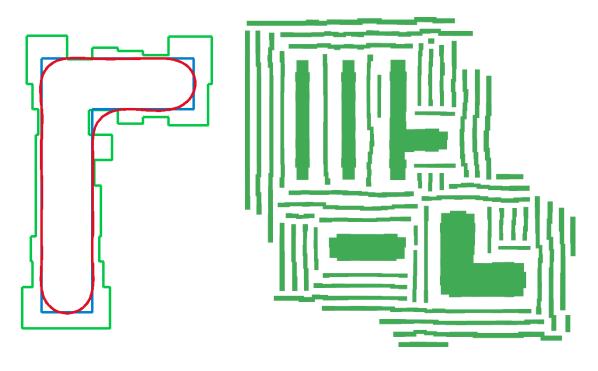


## DFM - Post-Layout Correction

- Optical-proximity-correction (OPC)
- Reticle-enhancement technology (RET)



https://www.spiedigitallibrary.org/journals/journal-of-micro-nanopatterning-materials-and-metrology/volume-15/issue-02/021009/Optical-proximity-correction-with-hierarchical-Bayes-model/10.1117/1.JMM.15.2.021009.full?SSO=1



https://en.wikipedia.org/wiki/Optical\_proximity\_correction

## Summary

- Design is not only for its functionality
- Design for test
- Design for manufacturability
- Design for reliability
- Design for quality

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